Abstracts

Modeling and Measurement of 1/f Noise Characteristics of Silicon BJTs

J.C. Costa, D. Ngo, R. Jackson, D. Lovelace, N. Camilleri and J. Jaffee. "Modeling and Measurement of 1/f Noise Characteristics of Silicon BJTs." 1994 MTT-S International Microwave Symposium Digest 94.2 (1994 Vol. II [MWSYM]): 1073-1076.

We present a method for measuring and extracting the BJT SPICE noise model parameters AF and KF based on an analysis of the general small signal equivalent circuit and the role of the BJT noise sources. Modeled and measured low-frequency noise data is presented for three high-frequency Motorola bipolar technologies.

❑ Return to main document.

Click on title for a complete paper.